

Safa Kasap

List of Publications by Year in descending order

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207
papers

4,616
citations

145106

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57
g-index

220
all docs

220
docs citations

220
times ranked

3007
citing authors

#	ARTICLE	IF	CITATIONS
1	RPL properties of samarium-doped CaSO ₄ . Japanese Journal of Applied Physics, 2022, 61, SB1035.	0.8	7
2	Direct conversion X-ray detectors with 70 pA cm ² dark currents coated from an alcohol-based perovskite ink. Journal of Materials Chemistry C, 2022, 10, 1228-1235.	2.7	12
3	The formation of a one-dimensional van der Waals selenium crystal from the three-dimensional amorphous phase: A spectroscopic signature of van der Waals bonding. Applied Physics Letters, 2022, 120, 033103.	1.5	2
4	Fluctuations in the collected charge in integrating photoconductive detectors under small and large signals: the variance problem. Journal Physics D: Applied Physics, 2022, 55, 345102.	1.3	0
5	Effects of Grain Boundaries on THz Conductivity in the Crystalline States of Ge ₂ Sb ₂ Te ₅ Phase-Change Materials: Correlation with DC Loss. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000411.	1.2	4
6	Size-Dependent Insulator-to-Metal and Metal-to-Insulator Phase Transitions in VO ₂ Microrods Grown on a Silicon Substrate. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100165.	0.8	0
7	Self-heating-induced electrical and optical switching in high quality VO ₂ films controlled with current pulses. Journal of Materials Science: Materials in Electronics, 2021, 32, 24285-24295.	1.1	1
8	X-Ray Photoconductivity of Stabilized Amorphous Selenium. , 2021, , 519-538.		1
9	Structural mapping of single-crystal VO ₂ microrods through metal-to-insulator phase transition. Journal of Materials Science, 2021, 56, 260-268.	1.7	1
10	Charge collection efficiency in the presence of non-uniform carrier drift mobilities and lifetimes in photoconductive detectors. Journal of Applied Physics, 2020, 128, .	1.1	28
11	Topology of conductive clusters in sputtered high-quality VO ₂ thin films on the brink of percolation threshold during insulator-to-metal and metal-to-insulator transitions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	11
12	Synthesis, structure and optical properties of high-quality VO ₂ thin films grown on silicon, quartz and sapphire substrates by high temperature magnetron sputtering: Properties through the transition temperature. Journal of Alloys and Compounds, 2020, 848, 156323.	2.8	33
13	Intense Anti-Stokes Emission from Erbium Ions in Gallium Lanthanum Sulphide-Oxide Glass in the Visible Spectral Range. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000448.	0.8	2
14	Effects of High-Dose X-Ray Irradiation on the Hole Lifetime in Vacuum-Deposited Stabilized a-Se Photoconductive Films: Implications to the Quality Control of a-Se Used in X-Ray Detectors. IEEE Transactions on Nuclear Science, 2020, 67, 2445-2453.	1.2	3
15	Frequency- and time-resolved photocurrents in vacuum-deposited stabilised a-Se films: the role of valence alternation defects. Journal of Materials Science: Materials in Electronics, 2020, 31, 15489-15504.	1.1	4
16	Electronic structure investigation of wide band gap semiconductors Mg ₂ PN ₃ and Zn ₂ PN ₃ : experiment and theory. Journal of Physics Condensed Matter, 2020, 32, 405504.	0.7	2
17	Dose profiles and x-ray energy optimization for microbeam radiation therapy by high-dose, high resolution dosimetry using Sm-doped fluoroaluminate glass plates and Monte Carlo transport simulation. Physics in Medicine and Biology, 2020, 65, 075010.	1.6	7
18	Radio-photoluminescence properties of LiCaAlF ₆ :Sm. Radiation Measurements, 2020, 132, 106251.	0.7	6

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19	Size, composition and alignment of VO ₂ microrod crystals by the reduction of V ₂ O ₅ thin films, and their optical properties through insulator-metal transitions. Journal of Alloys and Compounds, 2020, 827, 154150.	2.8	4
20	Enhancement of hardness in nanostructured CuO/TiO ₂ cement composites. SN Applied Sciences, 2020, 2, 1.	1.5	7
21	Effects of x-ray irradiation on charge transport and charge collection efficiency in stabilized a-Se photoconductors. Journal of Applied Physics, 2020, 127, .	1.1	13
22	The Effect of Substrate Biasing during DC Magnetron Sputtering on the Quality of VO ₂ Thin Films and Their Insulator-Metal Transition Behavior. Materials, 2019, 12, 2160.	1.3	10
23	Charge collection efficiency in photoconductive detectors under small to large signals. Journal of Applied Physics, 2019, 125, 244503.	1.1	11
24	Dark current-voltage characteristics of vacuum deposited multilayer amorphous selenium-alloy detectors and the effect of x-ray irradiation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	14
25	Optical and electrical properties of alkaline-doped and As-alloyed amorphous selenium films. Journal of Materials Science: Materials in Electronics, 2019, 30, 16833-16842.	1.1	7
26	Corrections to the Hecht collection efficiency in photoconductive detectors under large signals: non-uniform electric field due to drifting and trapped unipolar carriers. Journal Physics D: Applied Physics, 2019, 52, 135104.	1.3	12
27	X-ray induced Sm-ion valence conversion in Sm-ion implanted fluoroaluminate glasses towards high-dose radiation measurement. Journal of Materials Science: Materials in Electronics, 2019, 30, 16740-16746.	1.1	3
28	VO ₂ microrods synthesized from V ₂ O ₅ thin films. Applied Surface Science, 2019, 476, 259-264.	3.1	14
29	Further studies of radiation trapping in Er ³⁺ doped chalcogenide glasses. Optical Materials, 2019, 87, 157-163.	1.7	10
30	Radiation trapping in selected Er ³⁺ doped chalcogenide glasses and the extraction of the nonradiative lifetime. Optical Materials Express, 2019, 9, 2368.	1.6	2
31	Near-zero IR transmission of VO ₂ thin films deposited on Si substrate. Applied Surface Science, 2018, 440, 415-420.	3.1	15
32	Radiation-induced luminescence centres in Sm:MgF ₂ ceramics. Nuclear Instruments & Methods in Physics Research B, 2018, 435, 268-272.	0.6	20
33	Reversible superhydrophilicity and hydrophobicity switching of V ₂ O ₅ thin films deposited by magnetron sputtering. Applied Surface Science, 2018, 433, 1094-1099.	3.1	20
34	X-ray induced effects in the optical and thermal properties of a-Se _{1-x} As _x (x=0, 0.005, 0.06) doped with ¹³⁷ Cs. Journal of Materials Science: Materials in Electronics, 2017, 28, 7139-7150.	1.1	8
35	Radio-photoluminescence in Sm-doped BaF ₂ -Al ₂ O ₃ -B ₂ O ₃ glass-ceramics. Radiation Measurements, 2017, 106, 73-78.	0.7	37
36	Optical Properties of Electronic Materials: Fundamentals and Characterization. Springer Handbooks, 2017, , 1-1.	0.3	32

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37	Photoconductors for X-Ray Image Detectors. Springer Handbooks, 2017, , 1-1.	0.3	20
38	Solution-processed Er ³⁺ -doped As ₃ S ₇ chalcogenide films: optical properties and 1.5 μ m photoluminescence activated by thermal treatment. Journal of Materials Chemistry C, 2017, 5, 8489-8497.	2.7	10
39	Dynamics of radio-photoluminescence and thermally-stimulated luminescence in KBr:Sm. Journal of Materials Science: Materials in Electronics, 2017, 28, 15980-15986.	1.1	19
40	Thermal Properties and Thermal Analysis: Fundamentals, Experimental Techniques and Applications. Springer Handbooks, 2017, , 1-1.	0.3	6
41	Dynamics of Carrier Transport in Nanoscale Materials: Origin of Non-Drude Behavior in the Terahertz Frequency Range. Applied Sciences (Switzerland), 2016, 6, 50.	1.3	10
42	Aluminum Nitride Ceramic as an Optically Stimulable Luminescence Dosimeter Plate. Photonics, 2016, 3, 23.	0.9	13
43	Density of localized state distribution near the valence band in stabilized a-Se using interrupted field time of flight measurements with long interruption times. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1856-1863.	0.8	6
44	Radioluminescence properties of Sm-doped fluorochlorozirconate glasses and glass-ceramics. Japanese Journal of Applied Physics, 2016, 55, 02BC07.	0.8	16
45	Columnar recombination for X-ray generated electron-holes in amorphous selenium and its significance in a-Se x-ray detectors. Journal of Applied Physics, 2016, 119, .	1.1	19
46	Optically- and thermally-stimulated luminescences of Ce-doped SiO ₂ glasses prepared by spark plasma sintering. Optical Materials, 2016, 61, 15-20.	1.7	25
47	Characterization of vanadium oxide thin films with different stoichiometry using Raman spectroscopy. Thin Solid Films, 2016, 620, 64-69.	0.8	70
48	Radioluminescence and thermally-stimulated luminescence of SiO ₂ glasses prepared by spark plasma sintering. Journal of the Ceramic Society of Japan, 2016, 124, 541-545.	0.5	14
49	Sm-doped CsBr crystal as a new radio-photoluminescence (RPL) material. Journal of Rare Earths, 2016, 34, 769-773.	2.5	32
50	Charge transport in pure and stabilized amorphous selenium: re-examination of the density of states distribution in the mobility gap and the role of defects. Journal of Materials Science: Materials in Electronics, 2015, 26, 4644-4658.	1.1	29
51	Tailoring the 4I _{9/2} → ⁴ I _{13/2} emission in Er ³⁺ ions in different hosts media. Optical Materials, 2015, 41, 116-121.	1.7	6
52	Low-cost X-ray detectors. Nature Photonics, 2015, 9, 420-421.	15.6	16
53	Temperature dependence of charge carrier ranges in stabilized a-Se photoconductors. Canadian Journal of Physics, 2014, 92, 634-640.	0.4	9
54	ESR study of samarium doped fluorophosphate glasses for high-dose, high-resolution dosimetry. Optical Materials Express, 2014, 4, 1244.	1.6	22

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55	Optically erasable samarium-doped fluorophosphate glasses for high-dose measurements in microbeam radiation therapy. <i>Journal of Applied Physics</i> , 2014, 115, .	1.1	32
56	Samarium-doped Oxyfluoride Glass-Ceramic as a New Fast Erasable Dosimetric Detector Material for Microbeam Radiation Cancer Therapy Applications at the Canadian Synchrotron. <i>Journal of the American Ceramic Society</i> , 2014, 97, 2147-2153.	1.9	58
57	Origin of non-drude conductivity in the THz spectra of nanogranular semiconductors. , 2014, , .		0
58	Samarium-doped oxyfluoride borophosphate glasses for x-ray dosimetry in Microbeam Radiation Therapy. <i>Journal of Non-Crystalline Solids</i> , 2013, 377, 137-141.	1.5	13
59	Examination of the dynamic range of Sm-doped glasses for high-dose and high-resolution dosimetric applications in microbeam radiation therapy at the Canadian synchrotron. <i>Optical Materials</i> , 2013, 35, 1976-1980.	1.7	37
60	Response to "Comment on "The origin of non-Drude terahertz conductivity in nanomaterials" [Appl. Phys. Lett. 102, 096101 (2013)]. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	3
61	Terahertz and direct current losses and the origin of non-Drude terahertz conductivity in the crystalline states of phase change materials. <i>Journal of Applied Physics</i> , 2013, 114, 233105.	1.1	10
62	X-ray irradiation induced changes in electron transport in stabilized a-Se photoconductors. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	12
63	Measured and calculated K-fluorescence effects on the MTF of an amorphous-selenium based CCD x-ray detector. <i>Medical Physics</i> , 2012, 39, 608-622.	1.6	28
64	Non-Drude terahertz conductivity in nanomaterials: overview and applications to nanosilicon and nanogold. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 2602-2605.	0.8	3
65	X-ray induced Sm ³⁺ to Sm ²⁺ conversion in fluorophosphate and fluoroaluminate glasses for the monitoring of high-doses in microbeam radiation therapy. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	45
66	Dark current in multilayer stabilized amorphous selenium based photoconductive x-ray detectors. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	44
67	The origin of non-Drude terahertz conductivity in nanomaterials. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	33
68	Low-frequency noise in a-Se based x-ray photoconductors. , 2011, , .		3
69	Direct-Conversion X-Ray Detector Using Lateral Amorphous Selenium Structure. <i>IEEE Sensors Journal</i> , 2011, 11, 505-509.	2.4	17
70	Amorphous and Polycrystalline Photoconductors for Direct Conversion Flat Panel X-Ray Image Sensors. <i>Sensors</i> , 2011, 11, 5112-5157.	2.1	372
71	Optical properties of erbium-doped fluorochlorozirconate glasses. <i>Journal of Non-Crystalline Solids</i> , 2011, 357, 2475-2479.	1.5	15
72	Optical and selected thermal properties of samarium-doped fluorochlorozirconate (FCZ) glass-ceramics: Formation and growth of BaCl ₂ nanocrystals in FCZ glass-ceramics. <i>Journal of Non-Crystalline Solids</i> , 2011, 357, 2272-2277.	1.5	7

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73	Samarium-Doped Fluorochlorozirconate Glass-Ceramics as Red-Emitting X-Ray Phosphors. Journal of the American Ceramic Society, 2011, 94, 543-550.	1.9	36
74	Valency conversion of samarium ions under high dose synchrotron generated X-ray radiation. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2822-2825.	0.8	52
75	Trivalent Er and Sm ions in fluorochlorozirconate glasses: optical properties and X-ray luminescence. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2657-2660.	0.8	0
76	Photoinduced dichroism and the lack of a field effect. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2777-2779.	0.8	0
77	Spatially resolved measurement of high doses in microbeam radiation therapy using samarium doped fluorophosphate glasses. Applied Physics Letters, 2011, 99, .	1.5	77
78	Effect of repeated x-ray exposure on the resolution of amorphous selenium based x-ray imagers. Medical Physics, 2010, 37, 1339-1349.	1.6	24
79	Relaxation of the electrical properties of vacuum-deposited a-Se _{1-x} As _x photoconductive films: Charge-carrier lifetimes and drift mobilities. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 1145-1156.	0.9	16
80	Lateral metal-semiconductor-metal photodetectors based on amorphous selenium. Applied Physics Letters, 2009, 95, 013505.	1.5	35
81	Optical properties of amorphous silicon nitride thin-films prepared by VHF-PECVD using silane and nitrogen. Journal of Materials Science: Materials in Electronics, 2009, 20, 15-18.	1.1	10
82	Characterization of $4I_{9/2} \rightarrow 4F_{3/2}$ optical transitions in trivalent Nd ³⁺ ions in GaLaS glass. Journal of Materials Science: Materials in Electronics, 2009, 20, 19-22.	1.1	3
83	Excitation diffusion due to photon trapping in GeGaSe glasses heavily doped with Er ³⁺ . Journal of Materials Science: Materials in Electronics, 2009, 20, 139-143.	1.1	1
84	Lucky-drift model for impact ionization in amorphous semiconductors. Journal of Materials Science: Materials in Electronics, 2009, 20, 221-225.	1.1	29
85	The influence of CsBr addition on optical and thermal properties of GeGaS glasses doped with erbium. Journal of Materials Science: Materials in Electronics, 2009, 20, 421-424.	1.1	2
86	Electronic structure of hydrogenated amorphous Si _{1-x} N _x thin films using soft X-ray emission and absorption measurements. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 935-939.	0.8	0
87	Amorphous selenium and its alloys from early xeroradiography to high resolution X-ray image detectors and ultrasensitive imaging tubes. Physica Status Solidi (B): Basic Research, 2009, 246, 1794-1805.	0.7	135
88	Observation of $4F_{3/2} \rightarrow 4I_{15/2}$ radiative transition in Nd ³⁺ ions in GaLaS glass using frequency-resolved PL spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S54-S58.	0.8	2
89	Electronic and thermal properties of magnesium-doped a-Se films. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S98-S101.	0.8	4
90	Dark current in multilayer stabilized amorphous selenium X-ray photoconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S251-S254.	0.8	12

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91	X-Ray Detection Using a Two-Transistor Active Pixel Sensor Array Coupled to an a-Se X-Ray Photoconductor. IEEE Sensors Journal, 2009, 9, 51-56.	2.4	6
92	Evaluation of the x-ray response of amorphous selenium coated 100- $\frac{1}{4}$ m pitch a-Si active pixel sensors for tomosynthesis applications. , 2009, , .		0
93	Dependence of the electrical properties of stabilized a-Se on the preparation conditions and the development of a double layer X-ray detector structure. Current Applied Physics, 2008, 8, 383-387.	1.1	12
94	One-dimensional lucky-drift model with scattering and movement asymmetries for impact ionization in amorphous semiconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 796-799.	0.8	4
95	Optical and Photoluminescence Properties of Erbium-Doped Chalcogenide Glasses (GeGaS:Er). IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1353-1360.	1.9	27
96	Excitation diffusion in GeGaSe and GeGaS glasses heavily doped with Er ³⁺ . Optics Express, 2008, 16, 7709.	1.7	26
97	The Effects of Doping with Elements from the IIA Group on the Thermal and Electronic Properties of Amorphous Selenium. NATO Science for Peace and Security Series B: Physics and Biophysics, 2008, , 279-282.	0.2	1
98	X-ray Induced Effects on Photocurrents in Amorphous Se Films. Japanese Journal of Applied Physics, 2007, 46, L192-L195.	0.8	6
99	The dependence of the modulation transfer function on the blocking layer thickness in amorphous selenium x-ray detectors. Medical Physics, 2007, 34, 3358-3373.	1.6	8
100	Avalanche multiplication phenomenon in amorphous semiconductors: Amorphous selenium versus hydrogenated amorphous silicon. Journal of Applied Physics, 2007, 102, .	1.1	52
101	Recent photoluminescence research on chalcogenide glasses for photonics applications. Journal of Non-Crystalline Solids, 2007, 353, 1364-1371.	1.5	28
102	Slow luminescence from Er ³⁺ centers in Er-Doped GeGaSe chalcogenide glasses observed by wideband quadrature frequency-resolved spectroscopy. Journal of Materials Science: Materials in Electronics, 2007, 18, 97-101.	1.1	1
103	The kinetics of photo-induced dichroism in thin films of amorphous arsenic triselenide. Journal of Materials Science: Materials in Electronics, 2007, 18, 127-130.	1.1	4
104	Photoluminescence spectra and lifetimes of $\{^4\text{hbox}\{l\}_{\{13\}/2} \rightarrow ^4\text{hbox}\{l\}_{\{15\}/2}\}$ and $\{^4\text{hbox}\{l\}_{\{11\}/2} \rightarrow ^4\text{hbox}\{l\}_{\{15\}/2}\}$ transitions in erbium doped GeGaSe and GeGaS glasses. Journal of Materials Science: Materials in Electronics, 2007, 18, 153-157.	1.1	4
105	Optical and photoluminescence properties of Er-doped (GeSe ₂) _{1-x} (Ga ₂ Se ₃) _x bulk glasses. Journal of Materials Science: Materials in Electronics, 2007, 18, 231-234.	1.1	6
106	Optical properties vacuum deposited and chlorine doped a-Se thin films: aging effects. Journal of Materials Science: Materials in Electronics, 2007, 18, 429-433.	1.1	25
107	Effect of Ga on the structure of Ge-Se-Ga glasses from thermal analysis, Raman and XPS measurements. Journal of Materials Science: Materials in Electronics, 2007, 18, 367-370.	1.1	60
108	Thermal Properties and Thermal Analysis: . , 2006, , 385-408.		3

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109	Kinetics of the photostructural changes in a-Se films. Journal of Applied Physics, 2006, 100, 113506.	1.1	20
110	The effects of large signals on charge collection in radiation detectors: Application to amorphous selenium detectors. Journal of Applied Physics, 2006, 99, 124501.	1.1	26
111	Photoconductors for X-Ray Image Detectors. , 2006, , 1121-1137.		9
112	Ghosting mechanisms in a-Se based direct conversion x-ray image sensors. , 2005, , .		2
113	Ghosting caused by bulk charge trapping in direct conversion flat-panel detectors using amorphous selenium. Medical Physics, 2005, 32, 488-500.	1.6	48
114	Density of localized electronic states in a-Se from electron time-of-flight photocurrent measurements. Journal of Applied Physics, 2005, 97, 033706.	1.1	71
115	Sensitivity reduction mechanisms in amorphous selenium photoconductive x-ray image detectors. Applied Physics Letters, 2004, 85, 6430-6432.	1.5	19
116	X-ray-induced recombination effects in a-Se-based x-ray photoconductors used in direct conversion x-ray sensors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1005.	0.9	7
117	Characterization of Ag ₂ S ₂ Se and Ag ₂ S ₂ Se ₃ amorphous films prepared by pulsed laser deposition. Surface and Interface Analysis, 2004, 36, 1140-1143.	0.8	9
118	Lucky-drift model for avalanche multiplication in amorphous semiconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1186-1193.	0.8	24
119	Charge collection and absorption-limited x-ray sensitivity of pixellated x-ray detectors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 975.	0.9	19
120	Recombination of drifting holes with trapped electrons in stabilized a-Se photoconductors: Langevin recombination. Applied Physics Letters, 2004, 84, 1991-1993.	1.5	35
121	Lucky drift impact ionization in amorphous semiconductors. Journal of Applied Physics, 2004, 96, 2037-2048.	1.1	70
122	Small core rib waveguides with embedded gratings in As ₂ Se ₃ glass. Optics Express, 2004, 12, 6270.	1.7	40
123	High-resolution (20 cycles/mm) digital x-ray mammography using amorphous selenium directly coupled to CCD readout devices. , 2004, 5368, 466.		4
124	Conductance fluctuations in a-Si : H: effects of alloying and device structure. Journal of Materials Science: Materials in Electronics, 2003, 14, 693-696.	1.1	2
125	Dependence of charge-carrier ranges in stabilized a-Se on preparation conditions and alloying. Journal of Materials Science: Materials in Electronics, 2003, 14, 841-842.	1.1	10
126	Thermal and photoluminescence properties of Er ₂ S ₃ -doped (As ₂ Se ₃) ₉₀ (GaSe) ₅ Ge ₅ glasses. Journal of Materials Science: Materials in Electronics, 2003, 14, 851-852.	1.1	4

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127	Conductance fluctuations in VHF-PECVD grown hydrogenated microcrystalline silicon thin films. Journal of Materials Science: Materials in Electronics, 2003, 14, 731-732.	1.1	1
128	Rutherford backscattering spectroscopy of optically silver doped amorphous chalcogenides. European Physical Journal D, 2003, 53, A247-A256.	0.4	0
129	The influence of deposition conditions and alloying on the electronic properties of amorphous selenium. Semiconductors, 2003, 37, 789-794.	0.2	35
130	Strong Bragg gratings photoinduced by 633-nm illumination in evaporated As ₂ Se ₃ thin films. Optics Letters, 2003, 28, 459.	1.7	25
131	Modulation transfer function of photoconductive x-ray image detectors: effects of charge carrier trapping. Journal Physics D: Applied Physics, 2003, 36, 2352-2358.	1.3	27
132	Charge collection and absorption-limited sensitivity of x-ray photoconductors: Applications to a-Se and HgI ₂ . Applied Physics Letters, 2002, 80, 1664-1666.	1.5	93
133	Sensitivity of x-ray photoconductors: Charge trapping and absorption-limited universal sensitivity curves. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1082-1086.	0.9	30
134	1/f noise of amorphous indium oxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1027-1029.	0.9	2
135	DQE of photoconductive x-ray image detectors: application to a-Se. Journal Physics D: Applied Physics, 2002, 35, 2735-2743.	1.3	28
136	PHOTOLUMINESCENCE AND THERMAL PROPERTIES OF Er-DOPED As-Se-Ga-Ge BASED GLASSES. Nonlinear Optics, Quantum Optics, 2002, 29, 549-555.	0.2	14
137	Class transformation in vitreous As ₂ Se ₃ studied by conventional and temperature-modulated differential scanning calorimetry. Journal of Materials Research, 2001, 16, 2399-2407.	1.2	13
138	1/F NOISE IN UNDOPED HYDROGENATED AMORPHOUS SILICON AND SILICON-GERMANIUM ALLOYS. , 2001, , .		0
139	Title is missing!. Journal of Materials Science: Materials in Electronics, 2000, 11, 179-198.	1.1	121
140	Modelling of photoinduced discharge of photoreceptors under pulsed photoexcitation: small and large signal xerographic time-of-flight analysis. Journal Physics D: Applied Physics, 2000, 33, 449-463.	1.3	9
141	Photoconductor selection for digital flat panel x-ray image detectors based on the dark current. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 615-620.	0.9	17
142	Growth characteristics of vacuum coated thick a-Se films for device applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 665-670.	0.9	4
143	Properties of a-Se for use in flat panel X-ray image detectors. Journal of Non-Crystalline Solids, 2000, 266-269, 1163-1167.	1.5	27
144	1/f noise in p-type amorphous silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 661-664.	0.9	4

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145	Comparison of excess 1/f noise spectra in trimmed and untrimmed thick film resistors. International Journal of Electronics, 2000, 87, 1-9.	0.9	5
146	X-ray sensitivity of photoconductors: application to stabilized a-Se. Journal Physics D: Applied Physics, 2000, 33, 2853-2865.	1.3	331
147	Applications of Non-Crystalline Materials " B. AMORPHOUS CHALCOGENIDE PHOTOCONDUCTORS IN IMAGING TECHNOLOGIES. Series on Directions in Condensed Matter Physics, 2000, , 781-811.	0.1	3
148	The kinetics of the photo-induced solid-state chemical reaction in Ag/As ₃₃ S ₆₇ bilayers and its reaction products. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1999, 79, 223-237.	0.6	28
149	1/f-noise study of undoped intrinsic hydrogenated amorphous silicon thin films. Physical Review B, 1999, 60, 1477-1479.	1.1	12
150	Charge transport and electron-hole-pair creation energy in stabilized a-Se x-ray photoconductors. Journal Physics D: Applied Physics, 1999, 32, 200-207.	1.3	36
151	Amorphous chalcogenide Se _{1-x} Te _y semiconducting alloys: thermal and mechanical properties. Journal of Materials Science, 1999, 34, 3779-3787.	1.7	52
152	Title is missing!. Journal of Materials Science: Materials in Electronics, 1999, 10, 633-641.	1.1	9
153	Thermal properties of Sb _x Se _{100-x} glasses studied by modulated temperature differential scanning calorimetry. Journal of Non-Crystalline Solids, 1999, 248, 28-36.	1.5	46
154	Title is missing!. Journal of Materials Science Letters, 1998, 17, 1809-1811.	0.5	9
155	Title is missing!. Journal of Materials Science, 1998, 33, 5581-5588.	1.7	44
156	Metallic electrical contacts to stabilized amorphous selenium for use in X-ray image detectors. Journal of Non-Crystalline Solids, 1998, 227-230, 1359-1362.	1.5	31
157	X-ray sensitivity of a-Se for x-ray imaging with electrostatic readout. Journal of Applied Physics, 1998, 83, 2879-2887.	1.1	14
158	X-ray irradiation induced bulk space charge in stabilized a-Se x-ray photoconductors. Journal of Applied Physics, 1998, 84, 5495-5501.	1.1	11
159	<title>Flat panel detector for digital radiology using active matrix readout of amorphous selenium</title>. , 1997, 3032, 97.		5
160	Amorphous Semiconductors Usher in Digital X-Ray Imaging. Physics Today, 1997, 50, 24-30.	0.3	152
161	Glass transformation, heat capacity, and structure of Ge _x Se _{100-x} glasses studied by temperature-modulated differential scanning calorimetry experiments. Journal of Materials Research, 1997, 12, 1892-1899.	1.2	25
162	Electrical properties of thick film resistors from noise measurements. Journal of Materials Science Letters, 1997, 16, 1184-1186.	0.5	1

#	ARTICLE	IF	CITATIONS
163	Title is missing!. Journal of Materials Science, 1997, 32, 5889-5893.	1.7	9
164	Electrical properties of thick film resistors from noise measurements. Journal of Materials Science Letters, 1997, 16, 1184-1186.	0.5	3
165	Heat Capacity and the Structure of Chalcogenide Glasses by Modulated Differential Scanning Calorimetry (MDSC). Japanese Journal of Applied Physics, 1996, 35, L1116-L1119.	0.8	15
166	1/f conductance noise in n-type amorphous silicon. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1996, 73, 707-714.	0.6	20
167	Glass transformation, heat capacity and structure of AS _x Se _{1-x} glasses studied by modulated temperature differential scanning calorimetry experiments. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1996, 74, 667-680.	0.6	68
168	Langevin recombination of drifting electrons and holes in stabilized a-Se (Cl-doped a-Se: 0.3% As). The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1995, 71, 91-96.	0.6	30
169	Application of the interrupted field time-of-flight transient photoconductivity technique to investigating sample inhomogeneities: Cl-doped amorphous Se:Te and Se:As films. Canadian Journal of Physics, 1995, 73, 96-100.	0.4	8
170	Thermal Fatigue of Composites: Ultrasonic and SEM Evaluations. Journal of Engineering Materials and Technology, Transactions of the ASME, 1994, 116, 113-120.	0.8	16
171	The interrupted field time-of-flight transient photoconductivity technique for studying charge transport and trapping in high resistivity semiconductors. International Journal of Electronics, 1994, 76, 1029-1041.	0.9	7
172	An Experimental Study of Phase Transformations in an Al-Zn-Mg-Zr Alloy: DSC and Hot Microhardness Measurements. Canadian Metallurgical Quarterly, 1994, 33, 51-60.	0.4	12
173	Modelling of photoinduced discharge of double-layer photoreceptors: general formulation and small signal xerographic time-of-flight analysis. Journal Physics D: Applied Physics, 1994, 27, 574-581.	1.3	3
174	Method and apparatus for thermoacoustimetry: applications to polymers and glasses. Measurement Science and Technology, 1993, 4, 1213-1218.	1.4	9
175	Study of photogenerated charge carrier dispersion in chlorinated a-Se:0.3%As by the interrupted field time-of-flight technique. Applied Physics Letters, 1993, 63, 183-185.	1.5	9
176	Charge-carrier deep-trapping kinetics in high-resistivity semiconductors. Journal Physics D: Applied Physics, 1992, 25, 83-93.	1.3	7
177	Decay of Electrostatic Surface Potential on Insulators via Charge Injection, Transport and Trapping. Japanese Journal of Applied Physics, 1992, 31, 72-80.	0.8	10
178	Ultrasonic Evaluation of Thermal Fatigue of Composites. Journal of Engineering Materials and Technology, Transactions of the ASME, 1992, 114, 132-136.	0.8	7
179	A high-voltage interrupted-field time-of-flight transient photoconductivity apparatus. Measurement Science and Technology, 1991, 2, 75-80.	1.4	12
180	Deep-trapping kinematics of charge carriers in amorphous semiconductors: A theoretical and experimental study. Physical Review B, 1991, 43, 6691-6705.	1.1	16

#	ARTICLE	IF	CITATIONS
181	X-ray induced hole trapping in electroradiographic plates. Journal of Applied Physics, 1991, 69, 7087-7096.	1.1	37
182	Measurement of mobility-lifetime products in amorphous semiconductors. Canadian Journal of Physics, 1991, 69, 361-369.	0.4	13
183	Drift mobility relaxation in a-Se. Journal of Applied Physics, 1990, 67, 1918-1922.	1.1	20
184	An interrupted field time-of-flight (IFTOF) technique in transient photoconductivity measurements. Review of Scientific Instruments, 1990, 61, 2080-2087.	0.6	53
185	Glass transformation phenomena in bulk and film amorphous selenium via DSC heating and cooling scans. Journal of Materials Research, 1990, 5, 789-794.	1.2	17
186	Determination of the deep-hole capture cross-section in a-Se via xerographic and interrupted-field time-of-flight techniques. Philosophical Magazine Letters, 1990, 62, 377-382.	0.5	15
187	Thermal and mechanical properties of amorphous selenium films in the glass transformation region. Journal Physics D: Applied Physics, 1990, 23, 553-561.	1.3	9
188	Mechanical and thermal properties of the glassy semiconductor chlorinated $\text{Se}_{0.997}\text{As}_{0.003}$ used as an X-ray imaging material. Canadian Journal of Physics, 1989, 67, 686-693.	0.4	16
189	Transient photoconductivity measurements on halogenated a-Se Te_x photoconductors. Canadian Journal of Physics, 1989, 67, 1053-1064.	0.4	3
190	Dark decay of electrostatic surface potential on dielectrics via bulk space-charge buildup. Journal of Electrostatics, 1989, 22, 69-90.	1.0	20
191	Kinetics of structural relaxations in the glassy semiconductor a-Se. Journal of Materials Research, 1989, 4, 893-905.	1.2	29
192	Scientific instrumentation for hot microhardness measurements on amorphous solids. Review of Scientific Instruments, 1989, 60, 1321-1327.	0.6	8
193	Inverted xerographic depletion discharge mechanism for the dark decay of electrostatic surface potential on amorphous semiconductors. Journal of Applied Physics, 1988, 64, 450-452.	1.1	3
194	Hardness of polymeric glasses in the $T < T_g$ region: a-Se. Journal of Materials Research, 1988, 3, 609-612.	1.2	8
195	Method and apparatus for thermal microhardness analysis. Journal of Physics E: Scientific Instruments, 1988, 21, 932-935.	0.7	3
196	The demarcation energy concept in the analysis of charge carrier emission kinetics from deep mobility gap states in amorphous semiconductors. Journal Physics D: Applied Physics, 1988, 21, 841-844.	1.3	10
197	Method and apparatus for interrupted transit time transient photoconductivity measurements. Journal of Physics E: Scientific Instruments, 1988, 21, 1195-1202.	0.7	13
198	Evidence for field-assisted thermal emission of holes from deep mobility gap states in amorphous semiconductors from xerographic dark discharge measurements. Journal of Applied Physics, 1987, 62, 171-173.	1.1	11

#	ARTICLE	IF	CITATIONS
199	Thermal and mechanical properties of single- and double-layer amorphous $\text{Se}_{1-x}\text{Te}_x$ photoreceptors. <i>Journal of Materials Science Letters</i> , 1987, 6, 397-400.	0.5	8
200	Xerographic properties of single- and double-layer photoreceptors based on amorphous selenium-tellurium alloys. <i>Journal of Materials Science</i> , 1987, 22, 2569-2582.	1.7	17
201	Kinematical transformations in amorphous selenium alloys used in xerography. <i>Journal of Materials Science</i> , 1986, 21, 1329-1340.	1.7	79
202	Interface hole traps in double-layer amorphous semiconductor ($\text{Se}_{1-x}\text{Te}_x$) photoreceptor devices. <i>Semiconductor Science and Technology</i> , 1986, 1, 302-304.	1.0	4
203	Charge transport in amorphous xerographic photoreceptor films of chlorine-doped $\text{Se}_{0.995}\text{As}_{0.005}$. <i>Journal Physics D: Applied Physics</i> , 1985, 18, 721-729.	1.3	17
204	Time-of-flight drift mobility measurements on chlorine-doped amorphous selenium films. <i>Journal Physics D: Applied Physics</i> , 1985, 18, 703-720.	1.3	59
205	Theory of thermal analysis of non-isothermal crystallization kinetics of amorphous solids. <i>Journal of the Chemical Society, Faraday Transactions 2</i> , 1985, 81, 811.	1.1	24
206	Correction: Thickness dependence of electron transport in pure a-Se photoconductive films. <i>Canadian Journal of Physics</i> , 0, , 1-1.	0.4	0
207	The kinetics of the photo-induced solid-state chemical reaction in Ag/As ₃₃ S ₆₇ bilayers and its reaction products. , 0, .		3